

Silicon Carbide (SiC) MOSFET – EliteSiC, 20 mohm, 900 V, M2, TO-247-4L

NTH4L020N090SC1

Features

- Typ. $R_{DS(on)} = 20\text{ m}\Omega @ V_{GS} = 15\text{ V}$
Typ. $R_{DS(on)} = 16\text{ m}\Omega @ V_{GS} = 18\text{ V}$
- Ultra Low Gate Charge ($Q_{G(tot)} = 196\text{ nC}$)
- Low Effective Output Capacitance ($C_{oss} = 296\text{ pF}$)
- 100% UIL Tested
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb-Free 2LI (on second level interconnection)

Typical Applications

- UPS
- DC-DC Converter
- Boost Inverter

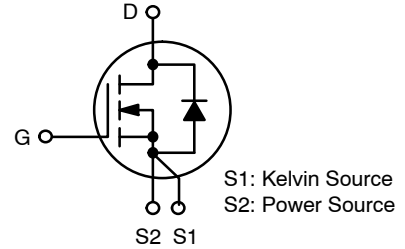
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	900	V	
Gate-to-Source Voltage		V_{GS}	+22/-8	V	
Recommended Operation Values of Gate-Source Voltage		$T_C < 175^\circ\text{C}$ V_{GSop}	+15/-5	V	
Continuous Drain Current $R_{\theta JC}$	Steady State	$T_C = 25^\circ\text{C}$	I_{DC}	116	A
			Power Dissipation $R_{\theta JC}$	P_{DC}	484
Continuous Drain Current $R_{\theta JC}$	Steady State	$T_C = 100^\circ\text{C}$	I_{DC}	82	A
			Power Dissipation $R_{\theta JC}$	P_{DC}	242
Pulsed Drain Current (Note 2)		$T_A = 25^\circ\text{C}$	I_{DM}	504	A
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	106	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_L = 23\text{ A}_{pk}, L = 1\text{ mH}$) (Note 3)		E_{AS}	264	mJ	

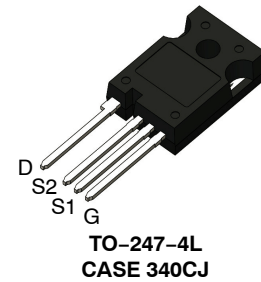
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. E_{AS} of 162 mJ is based on starting $T_J = 25^\circ\text{C}$; $L = 1\text{ mH}$, $I_{AS} = 23\text{ A}$, $V_{DD} = 100\text{ V}$, $V_{GS} = 15\text{ V}$.

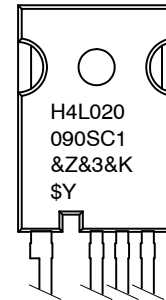
$V_{(BR)DSS}$	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
900 V	28 m Ω @ 15 V	118 A



N-CHANNEL MOSFET



MARKING DIAGRAM



- H4L020090SC1 = Specific Device Code
- &Z = Assembly Plant Code
- &3 = Date Code (Year & Week)
- &K = Lot
- \$Y = onsemi Logo

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

NTH4L020N090SC1

Table 1. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-to-Case (Note 1)	$R_{\theta JC}$	0.31	$^{\circ}C/W$
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	40	$^{\circ}C/W$

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 V, I_D = 1 mA$	900			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 1 mA$, refer to $25^{\circ}C$		500		$mV/^{\circ}C$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0 V, V_{DS} = 900 V$	$T_J = 25^{\circ}C$		100	μA
			$T_J = 175^{\circ}C$		250	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = +22/-8 V, V_{DS} = 0 V$			± 1	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 20 mA$	1.8	2.7	4.3	V
Recommended Gate Voltage	V_{GOP}		-5		+15	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 15 V, I_D = 60 A, T_J = 25^{\circ}C$		20	28	m Ω
		$V_{GS} = 18 V, I_D = 60 A, T_J = 25^{\circ}C$		16		
		$V_{GS} = 15 V, I_D = 60 A, T_J = 175^{\circ}C$		27		
Forward Transconductance	g_{FS}	$V_{DS} = 20 V, I_D = 60 A$		49		S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS} = 0 V, f = 1 MHz, V_{DS} = 450 V$		4415		pF
Output Capacitance	C_{OSS}			296		
Reverse Transfer Capacitance	C_{RSS}			24		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -5/15 V, V_{DS} = 720 V, I_D = 60 A$		196		nC
Threshold Gate Charge	$Q_{G(TH)}$			42		
Gate-to-Source Charge	Q_{GS}			78		
Gate-to-Drain Charge	Q_{GD}			55		
Gate-Resistance	R_G		$f = 1 MHz$		1.6	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5/15 V, V_{DS} = 720 V, I_D = 60 A, R_G = 2.5 \Omega, \text{Inductive Load}$		29		ns
Rise Time	t_r			28		
Turn-Off Delay Time	$t_{d(OFF)}$			54		
Fall Time	t_f			14		
Turn-On Switching Loss	E_{ON}			611		μJ
Turn-Off Switching Loss	E_{OFF}			293		
Total Switching Loss	E_{TOT}			904		
DRAIN-SOURCE DIODE CHARACTERISTICS						
Continuous Drain-Source Diode Forward Current	I_{SD}	$V_{GS} = -5 V, T_J = 25^{\circ}C$			106	A
Pulsed Drain-Source Diode Forward Current (Note 2)	I_{SDM}	$V_{GS} = -5 V, T_J = 25^{\circ}C$			504	A
Forward Diode Voltage	V_{SD}	$V_{GS} = -5 V, I_{SD} = 30 A, T_J = 25^{\circ}C$		3.8		V

NTH4L020N090SC1

Table 2. ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise stated) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS						
Reverse Recovery Time	t_{RR}	$V_{GS} = -5/15\text{ V}$, $I_{SD} = 60\text{ A}$, $di_S/dt = 1000\text{ A}/\mu\text{s}$, $V_{DS} = 720\text{ V}$		30		ns
Reverse Recovery Charge	Q_{RR}			244		nC
Reverse Recovery Energy	E_{REC}			11		μJ
Peak Reverse Recovery Current	I_{RRM}			16		A
Charge Time	T_a			17		ns
Discharge Time	T_b			13		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

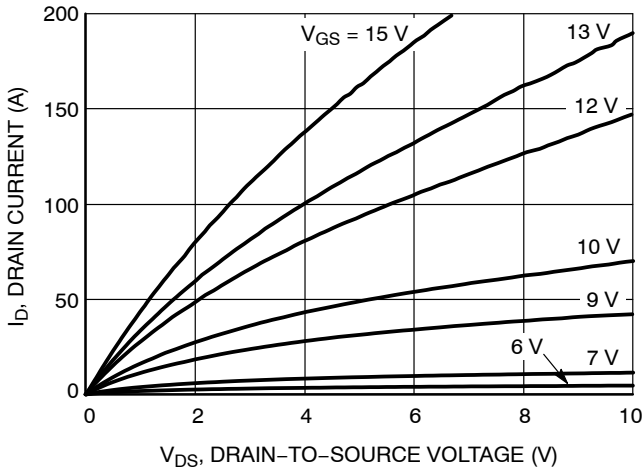


Figure 1. On-Region Characteristics

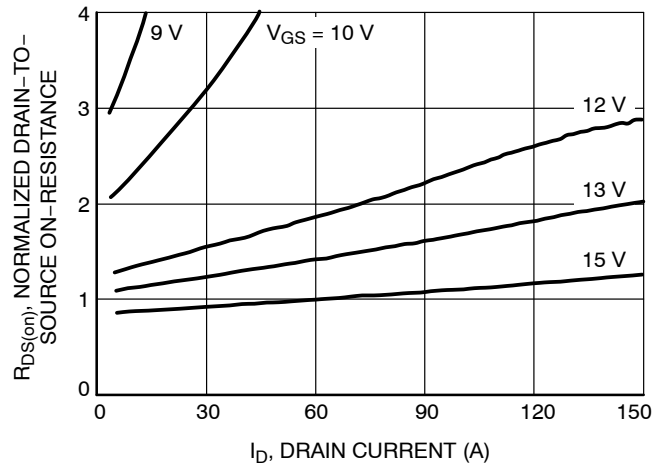


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

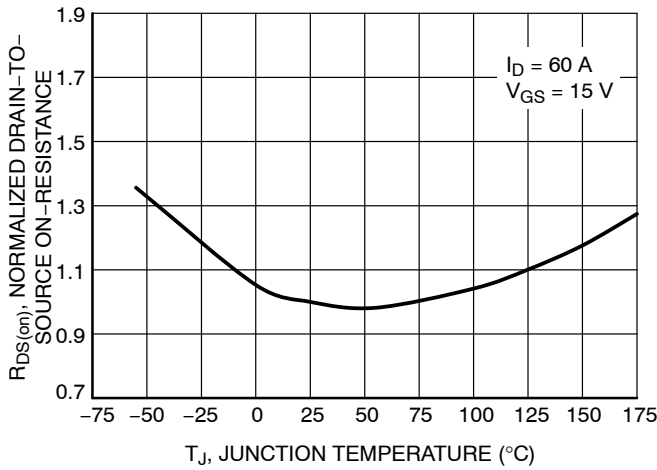


Figure 3. On-Resistance Variation with Temperature

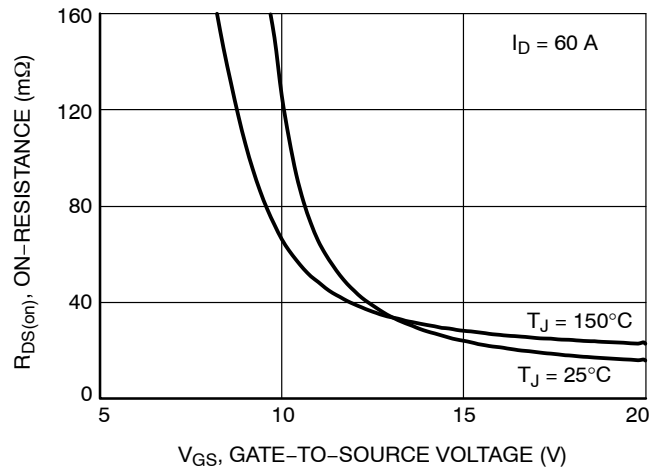


Figure 4. On-Resistance vs. Gate-to-Source Voltage

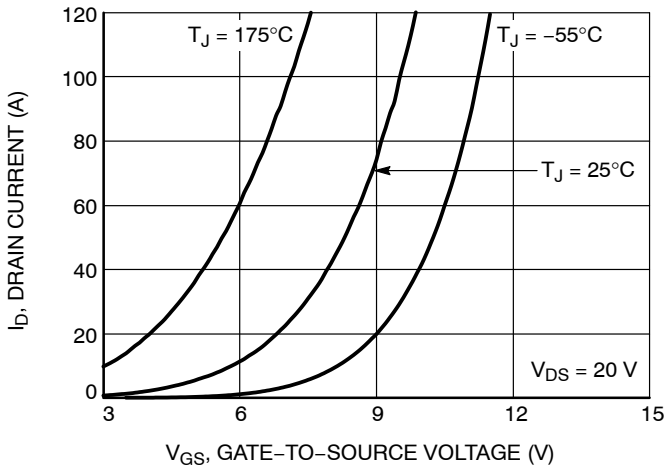


Figure 5. Transfer Characteristics

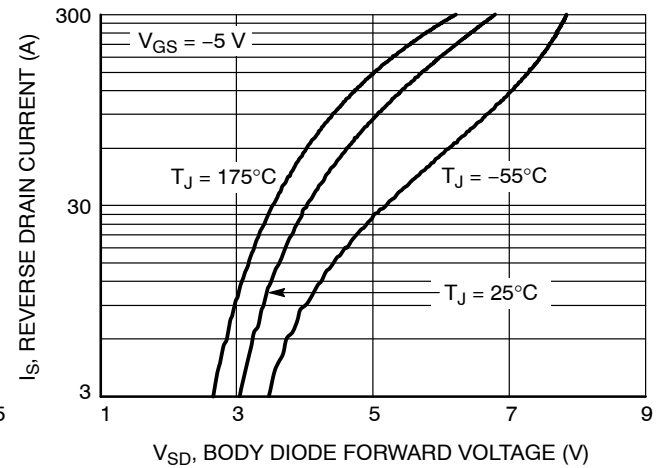


Figure 6. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS (continued)

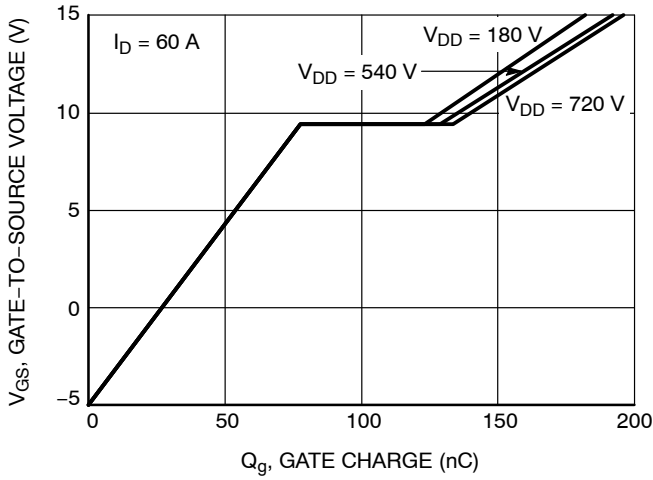


Figure 7. Gate-to-Source Voltage vs. Total Charge

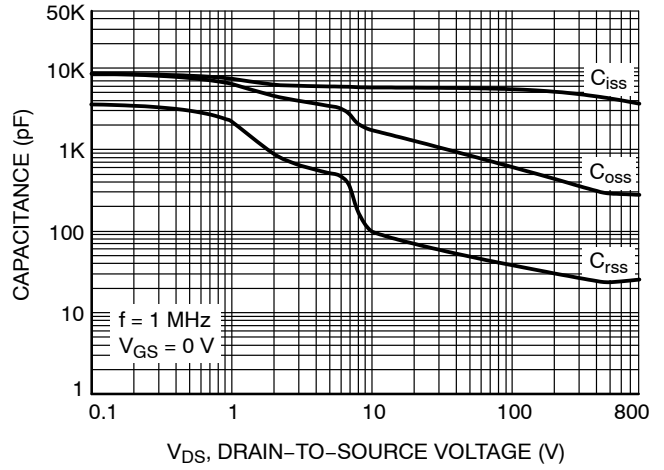


Figure 8. Capacitance vs. Drain-to-Source Voltage

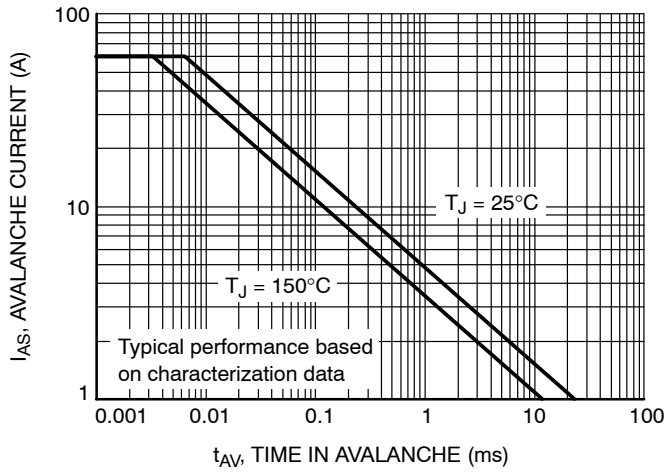


Figure 9. Unclamped Inductive Switching Capability

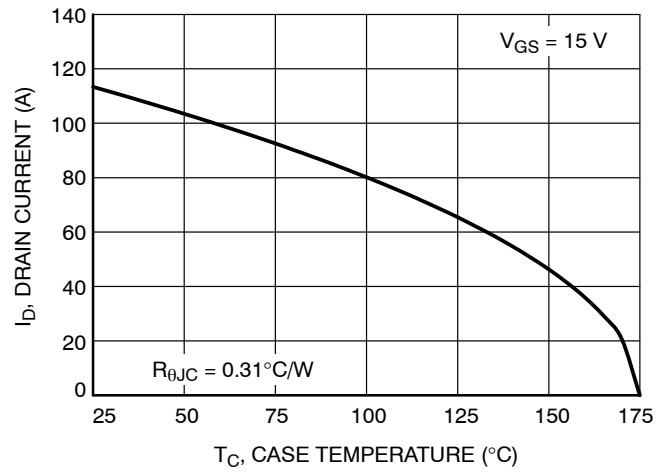


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

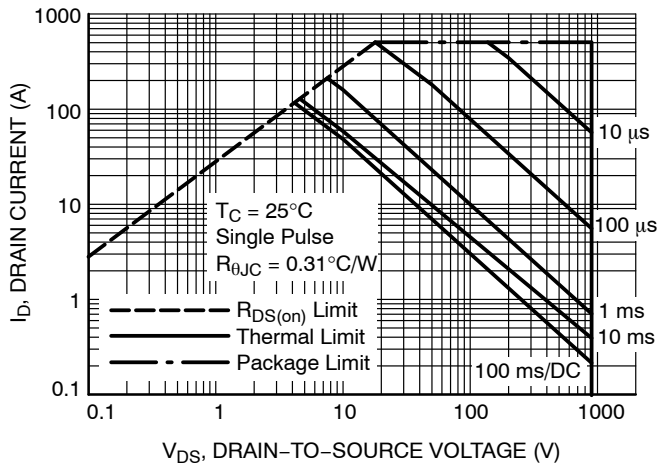


Figure 11. Safe Operating Area

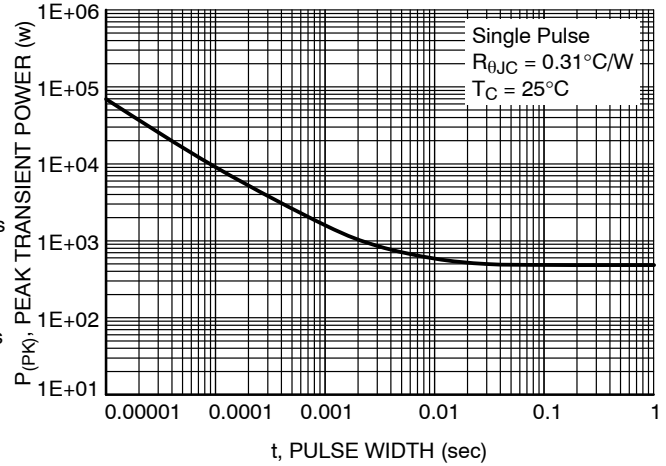


Figure 12. Single Pulse Maximum Power Dissipation

NTH4L020N090SC1

TYPICAL CHARACTERISTICS (continued)

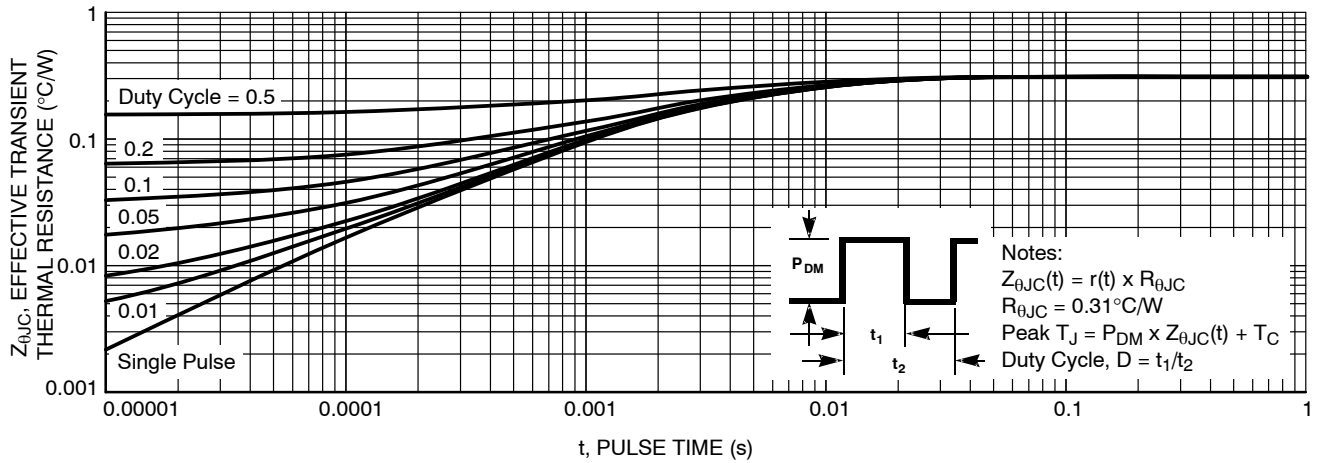


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Quantity
NTH4L020N090SC1	H4L020090SC1	TO-247-4L	Tube	30 Units

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-4LD
CASE 340CJ
ISSUE A

DATE 16 SEP 2019



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.10	2.40	2.70
A2	1.80	2.00	2.20
b	1.07	1.20	1.33
b1	1.20	1.40	1.60
b2	2.02	2.22	2.42
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.25	16.50
D2	0.97	1.17	1.37
e	2.54 BSC		
e1	5.08 BSC		
E	15.40	15.60	15.80
E1	12.80	13.00	13.20
E/2	4.80	5.00	5.20
L	18.22	18.42	18.62
L1	2.42	2.62	2.82
p	3.40	3.60	3.80
p1	6.60	6.80	7.00
Q	5.97	6.17	6.37
S	5.97	6.17	6.37

NOTES:

- A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5-2009.

DOCUMENT NUMBER:	98AON13852G	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-247-4LD	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales